

# 2SA1267

## PNP Silicon Epitaxial Planar Transistor

for switching and AF amplifier applications.

The transistor is subdivided into three groups, O, Y and G according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



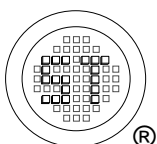
1. Emitter 2. Collector 3. Base  
TO-92 Plastic Package

### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	50	V
Collector Emitter Voltage	$-V_{CEO}$	50	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	150	mA
Emitter Current	$I_E$	150	mA
Power Dissipation	$P_{tot}$	400	mW
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 55 to + 150	$^\circ\text{C}$

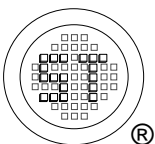
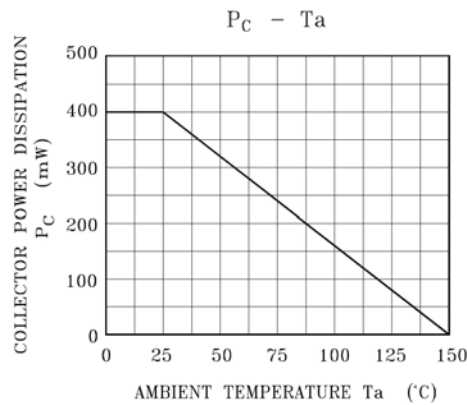
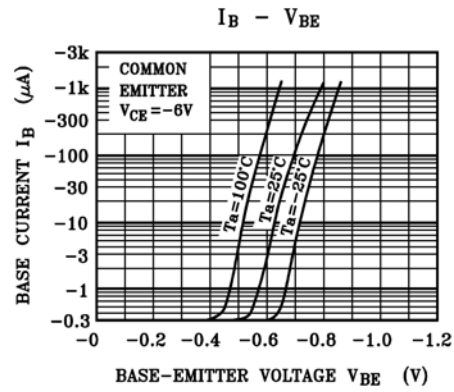
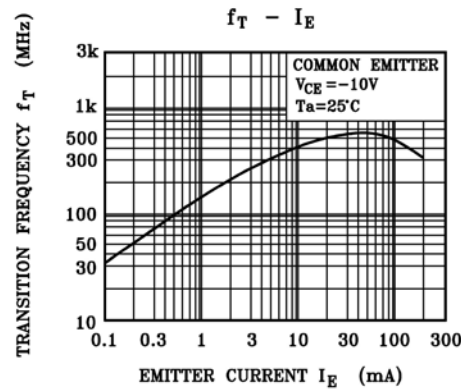
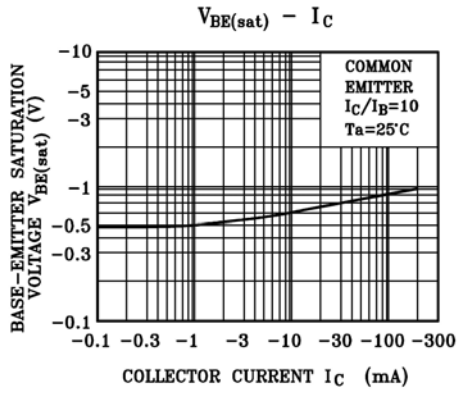
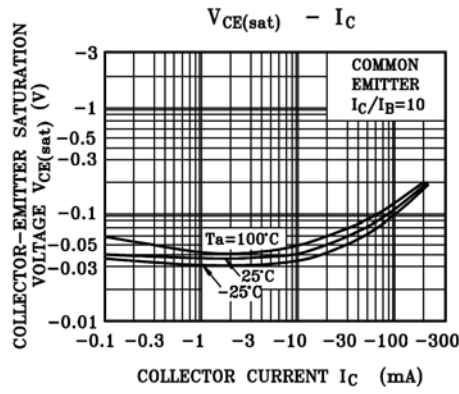
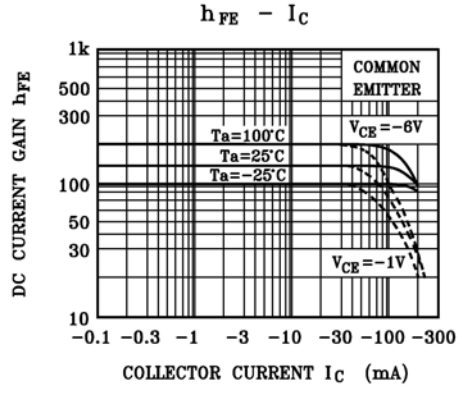
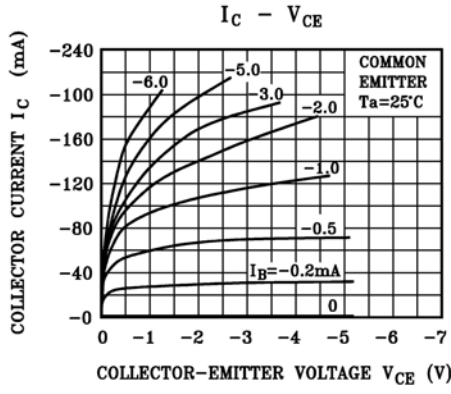
### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit	
DC Current Gain at $-V_{CE} = 6\text{ V}$ , $-I_C = 2\text{ mA}$	Current Gain Group O	$h_{FE}$	70	140	-
	Y	$h_{FE}$	120	240	-
	G	$h_{FE}$	200	400	-
Collector Base Cutoff Current at $-V_{CB} = 50\text{ V}$	$-I_{CBO}$	-	100	nA	
Emitter Base Cutoff Current at $-V_{EB} = 5\text{ V}$	$-I_{EBO}$	-	100	nA	
Collector Emitter Saturation Voltage at $-I_C = 100\text{ mA}$ , $-I_B = 10\text{ mA}$	$-V_{CE(sat)}$	-	0.3	V	
Transition Frequency at $-V_{CE} = 10\text{ V}$ , $-I_C = 1\text{ mA}$	$f_T$	80	-	MHz	
Collector Output Capacitance at $-V_{CB} = 10\text{ V}$ , $f = 1\text{ MHz}$	$C_{ob}$	-	7	pF	



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